

METHOD FOR TREATING NITRIDE SEMICONDUCTOR AND NITRIDE SEMICONDUCTOR AS WELL AS NITRIDE SEMICONDUCTOR ELEMENT

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- european:

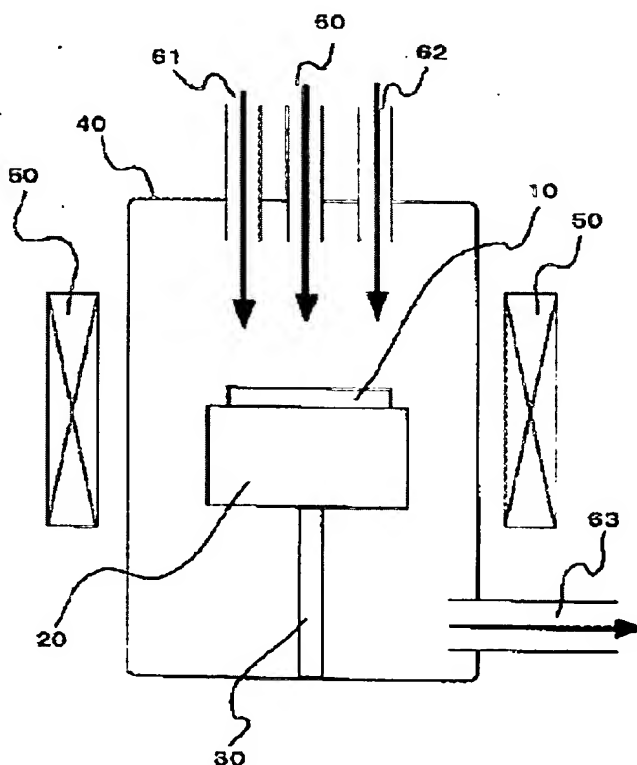
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Abstract of JP2003031552

PROBLEM TO BE SOLVED: To improve surface morphology of a nitride semiconductor or its polishing damage. **SOLUTION:** A method for treating the nitride semiconductor comprises a step of heating the nitride semiconductor, and a step of introducing chlorine gas, an atmospheric gas and ammonia gas.



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